


PTO-1449 REPRODUCED SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION November 4, 2004 (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002	APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003
	EXAMINER Nhu, David	CONFIRMATION NO. 8117	GROUP 2818

U.S. PATENT DOCUMENTS				
EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
DN	AC8	6,495,862 B1	12-17-2002	Okazaki <i>et al.</i>
	AD8	US 2001/0032976 A1	10-25-2001	Ishikawa <i>et al.</i>
	AE8	US 2002/0001864 A1	01-03-2002	Ishikawa <i>et al.</i>
	AF8	US 2002/0182765 A1	12-05-2002	Tran <i>et al.</i>
	AG8	6,403,987 B1	06-11-2002	Miki <i>et al.</i>
	AH8	US2002/0047128 A1	04-25-2002	Song <i>et al.</i>
	AI8	6,344,665 B1	02-05-2002	Sung <i>et al.</i>
	AJ8	6,417,525 B1	07-09-2002	Hata
	AK8	5,760,423	06-02-1998	Kamakura <i>et al.</i>
	AA9	6,268,618 B1	07-31-2001	Miki <i>et al.</i>
	AB9	5,656,832	08-12-1997	Ohba <i>et al.</i>
	AC9	5,834,331	11-10-1998	Razeghi
	AD9	5,900,650	05-04-1999	Nitta
	AE9	6,153,894	11-28-2000	Udagawa
	AF9	6,118,801	09-12-2000	Ishikawa <i>et al.</i>
	AC9	6,521,999 B1	02-18-2003	Uemura <i>et al.</i>
	AH9	5,877,558	03-02-1999	Nakamura <i>et al.</i>
	AI9	5,455,195	10-03-1995	Ramsey <i>et al.</i>
	AJ9	6,531,383 B1	03-11-2003	Lee
	AK9	6,445,127 B1	09/03/2002	Oku, <i>et al.</i>
	AA10	6,410,942 B1	06-25-2002	Thibeault, <i>et al.</i>
	AB10	5,726,462	03-10-1998	Spahn, <i>et al.</i>
	AC10	6,060,335	05-09-2000	Rennie, <i>et al.</i>
	AD10	6,287,947 B1	09-11-2001	Ludowise, <i>et al.</i>
	AE10	5,442,205	08-15-1995	Brasen, <i>et al.</i>
DN	AF10	5,637,530	06-10-1997	Gaines, <i>et al.</i>

EXAMINER	DATE CONSIDERED
----------	-----------------

PTO-1449 REPRODUCED SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION November 4, 2004 (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Nhu, David	CONFIRMATION NO. 8117	GROUP 2818	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AV6		Chichibu, S., <i>et al.</i> , "Exciton Localization in InGaN Quantum Well Devices," <i>J. Vac. Sci. Technol B.</i> , Vol. 16(4):2204-2214 (1998).
AW6		Chen, L., <i>et al.</i> , "Fabrication of 50-100 nm Patterned InGaN Blue Light Emitting Heterostructures," <i>IEEE, 14th Annual Meeting of the IEEE Lasers & Electro-Optics Society</i> , 1:760-761 (2001).
AX6		Cho, H. K., <i>et al.</i> , "Influence of Strain-Induced Indium Clustering on Characteristics of InGaN/GaN Multiple Quantum Wells with High Indium Composition," <i>Journal of Applied Physics</i> , 91(3):1104-1107 (2002).
AY6		Narayan, J. and H. Wang, "Effect of Thickness Variation in High-Efficiency InGaN/GaN Light-Emitting Diodes," <i>Applied Physics Letters</i> , 81(5): 841-843 (2002).
AZ6		Kim, H., <i>et al.</i> , "Design and Fabrication of Highly Efficient GaN-Based Light-Emitting Diodes," <i>IEEE Transactions on Electron Devices</i> , 49(10):1715-1722 (2002).
AR7		Maeda, T., <i>et al.</i> , "Effects of NiO on Electrical Properties of NiAu-Based Ohmic Contacts for <i>p</i> -type GaN," <i>Applied Physics Letters</i> 75(26):4145-4147 (1999).

EXAMINER 	DATE CONSIDERED 11/24/04
---	-----------------------------